PNP Epitaxial Planar Silicon Transistor

CPH5514

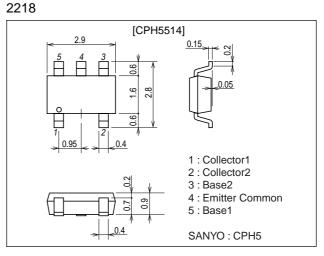
Switching Applications (with Bias Resistance)

Features

- On-chip bias resistance (R1=10k Ω , R2=10k Ω).
- Composite type with 2 transistors contained in the CPH package currently in use, improving the mounting efficiency greatly.
- The CPH5514 is formed with two chips, being equivalent to the 2SA1344, placed in one package.
- Excellent in thermal equilibrium and pair capability.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-50	V
Collector-to-Emitter Voltage	VCEO		-50	V
Emitter-to-Base Voltage	VEBO		-10	V
Collector Current	IC		-100	mA
Collector Current (Pulse)	ICP		-200	mA
Collector Dissipation	PC	1unit	350	mW
Total Power Dissipation	Рт		500	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Ofine
Collector Cutoff Current	ICBO	V _{CB} =-40V, I _E =0			-0.1	μΑ
	ICEO	V _{CE} =-40V, I _E =0			-0.5	μA
Emitter Cutoff Current	IEBO	V _{EB} =-5V, I _C =0	-170	-250	-360	μA
DC Current Gain	hFE	VCE=-5V, IC=-10mA	50			
Gain-Bandwidth Product	fΤ	V _{CE} =-10V, I _C =-5mA		200		MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		5.1		pF
Note : The specifications shown above are for each individual transistor.			Continued on next page.			

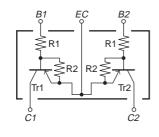
Marking: 3U

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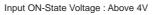
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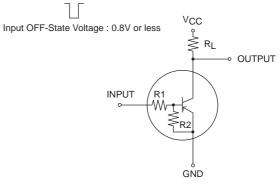
Parameter	Symbol	Conditions	Ratings			- Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	IC=-10mA, IB=-0.5mA		-1.0	-0.3	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =-10μA, I _E =0	-50			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=-100μA, RBE=∞	-50			V
Input OFF-State Voltage	VI(off)	V _{CE} =-5V, I _C =-100µA	-0.8	-1.1	-1.5	V
Input ON-State Voltage	Vj(on)	V _{CE} =-0.2V, I _C =-10mA	-1.0	-2.0	-4.0	V
Input Resistance	R1		7.0	10	13	kΩ
Resistance Ratio	R1 / R2		0.9	1.0	1.1	

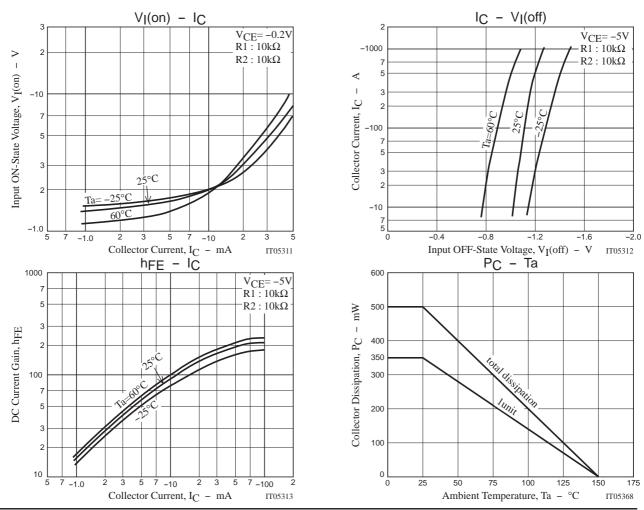
Electrical Connection



Application Circuit Example







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